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[ON Semiconductor](#)
[NTLUF4189NZTBG](#)

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NTLUF4189NZ

Power MOSFET and Schottky Diode

30 V, N-Channel with 0.5 A Schottky Barrier Diode, 1.6 x 1.6 x 0.55 mm μ Cool™ Package

Features

- Low Qg and Capacitance to Minimize Switching Losses
- Low Profile UDFN 1.6x1.6 mm for Board Space Saving
- Low VF Schottky Diode
- ESD Protected Gate
- This is a Halide-Free Device
- This is a Pb-Free Device

Applications

- DC-DC Boost Converter
- Color Display and Camera Flash Regulators
- Optimized for Power Management Applications for Portable Products, such as Cell Phones, PMP, DSC, GPS, and others

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V _{DSS}	30	V
Gate-to-Source Voltage			V _{GS}	±8.0	V
Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	1.5	A
		T _A = 85°C		1.1	
	t ≤ 5 s	T _A = 25°C		1.9	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	0.8	W
	t ≤ 5 s	T _A = 25°C		1.3	
Continuous Drain Current (Note 2)	Steady State	T _A = 25°C	I _D	1.2	A
		T _A = 85°C		0.9	
Power Dissipation (Note 2)		T _A = 25°C	P _D	0.5	W
Pulsed Drain Current		tp = 10 μs	I _{DM}	8.0	A
MOSFET Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to 150	°C
Schottky Operating Junction & Storage Temperature			T _J , T _{STG}	-55 to 125	°C
Source Current (Body Diode) (Note 2)			I _S	1.5	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C
Gate-to-Source ESD Rating (HBM) per JESD22-A114F			ESD	1000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.



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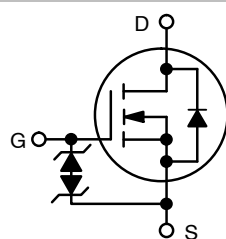
<http://onsemi.com>

MOSFET

V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
30 V	200 mΩ @ 4.5 V	1.5 A
	250 mΩ @ 3.0 V	0.5 A
	350 mΩ @ 2.5 V	0.5 A

SCHOTTKY DIODE

V _R MAX	V _F TYP	I _F MAX
30 V	0.52 V	0.5 A



N-Channel MOSFET

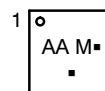


Schottky Diode

MARKING DIAGRAM

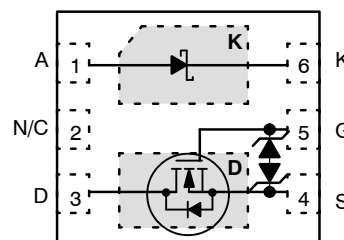


UDFN6
CASE 517AT
 μ COOL™



AA = Specific Device Code
M = Date Code
■ = Pb-Free Package

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NTLUF4189NZ

DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTLUF4189NZTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUF4189NZTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Schottky Diode Maximum Ratings (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Value	Units
Peak Repetitive Reverse Voltage	V _{RRM}	30	V
DC Blocking Voltage	V _R	30	V
Average Rectified Forward Current	I _F	0.5	A

Thermal Resistance Ratings

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 3)	R _{θJA}	155	°C/W
Junction-to-Ambient – t ≤ 5 s (Note 3)	R _{θJA}	100	
Junction-to-Ambient – Steady State min Pad (Note 4)	R _{θJA}	245	

MOSFET Electrical Characteristics (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = 250 μA, ref to 25°C		22		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V			1.0	μA
					10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8.0 V			10	μA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.4	1.1	1.5	V
Negative Threshold Temp. Coefficient	V _{GS(TH)} /T _J			3.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 1.5 A		145	200	mΩ
		V _{GS} = 3.0 V, I _D = 0.5 A		185	250	
		V _{GS} = 2.5 V, I _D = 0.5 A		220	350	
Forward Transconductance	g _{FS}	V _{DS} = 4.0 V, I _D = 0.15 A		1.1		S

CHARGES & CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V		95		pF
Output Capacitance	C _{OSS}			15		
Reverse Transfer Capacitance	C _{RSS}			10		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 1.5 A		1.4	3.0	nC
Threshold Gate Charge	Q _{G(TH)}			0.2		
Gate-to-Source Charge	Q _{GS}			0.4		
Gate-to-Drain Charge	Q _{GD}			0.4		

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)

4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

6. Switching characteristics are independent of operating junction temperatures

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MOSFET Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 6)						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DD} = 15\text{ V},$ $I_D = 1\text{ A}, R_G = 6\ \Omega$		7.0		ns
Rise Time	t_r			4.5		
Turn-Off Delay Time	$t_{d(OFF)}$			10.2		
Fall Time	t_f			1.2		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 1\text{ A}$	$T_J = 25^\circ\text{C}$		0.8	1.2	V
			$T_J = 85^\circ\text{C}$		0.75		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_{SD}/dt = 100\text{ A}/\mu\text{s},$ $I_S = 1\text{ A}$			10.5		ns
Charge Time	t_a				8.9		
Discharge Time	t_b				1.6		
Reverse Recovery Charge	Q_{RR}				2.1		nC

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Maximum Instantaneous Forward Voltage	V_F	$I_F = 10\text{ mA}$		0.27	0.37	V
		$I_F = 100\text{ mA}$		0.36	0.46	
		$I_F = 500\text{ mA}$		0.52	0.62	
Maximum Instantaneous Reverse Current	I_R	$V_R = 10\text{ V}$		2.0	10	μA
		$V_R = 30\text{ V}$		20	200	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 85^\circ\text{C}$ unless otherwise specified)

Maximum Instantaneous Forward Voltage	V_F	$I_F = 10\text{ mA}$		0.2		V
		$I_F = 100\text{ mA}$		0.3		
		$I_F = 500\text{ mA}$		0.51		
Maximum Instantaneous Reverse Current	I_R	$V_R = 10\text{ V}$		80		μA
		$V_R = 30\text{ V}$		525		

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 125^\circ\text{C}$ unless otherwise specified)

Maximum Instantaneous Forward Voltage	V_F	$I_F = 10\text{ mA}$		0.14		V
		$I_F = 100\text{ mA}$		0.27		
		$I_F = 500\text{ mA}$		0.51		
Maximum Instantaneous Reverse Current	I_R	$V_R = 10\text{ V}$		600		μA
		$V_R = 30\text{ V}$		3000		

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Capacitance	C	$V_R = 5\text{ V}, f = 1.0\text{ MHz}$		6.0		pF
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- Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)
- Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz. Cu.
- Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$
- Switching characteristics are independent of operating junction temperatures

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TYPICAL MOSFET CHARACTERISTICS

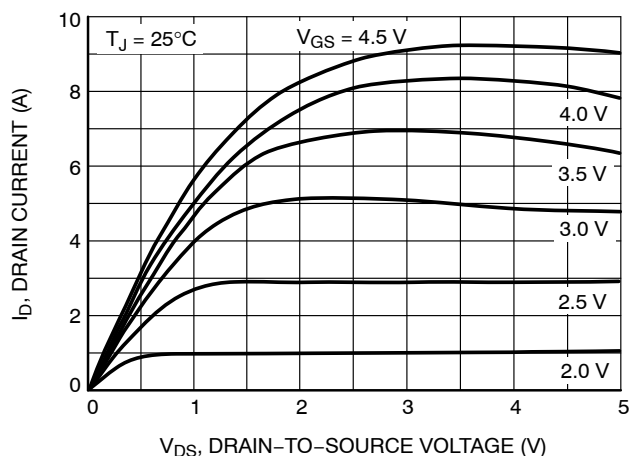


Figure 1. On-Region Characteristics

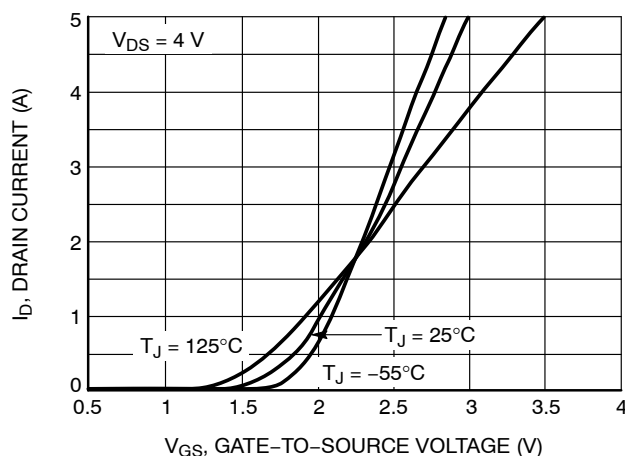


Figure 2. Transfer Characteristics

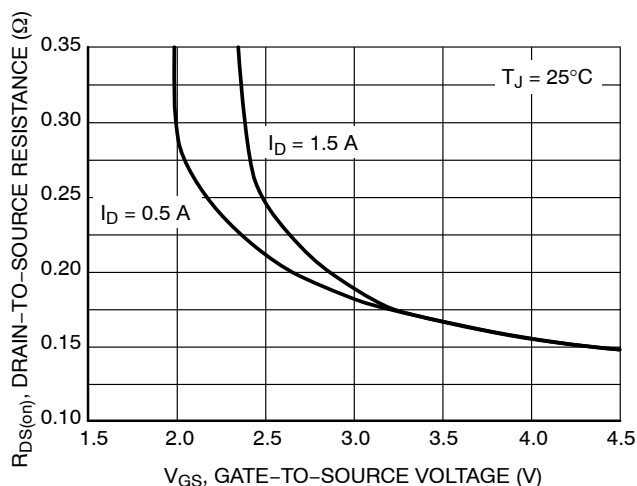


Figure 3. On-Resistance vs. Gate Voltage

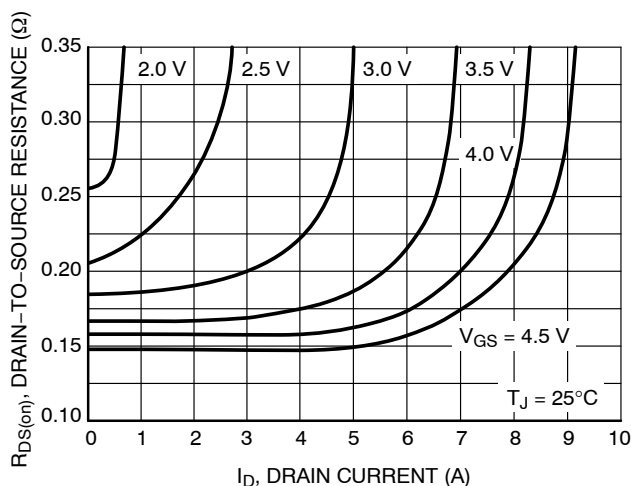


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

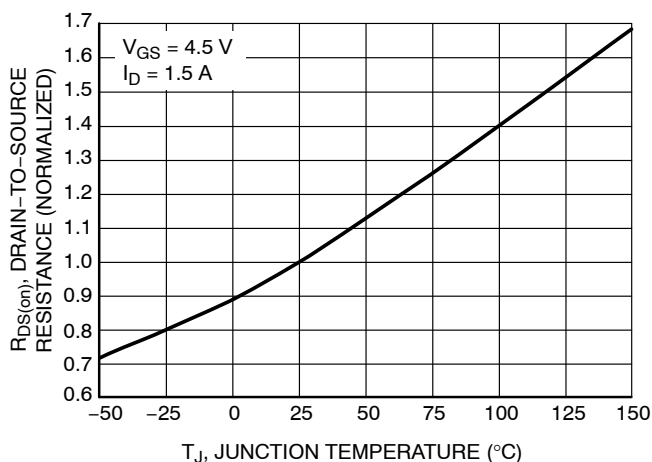


Figure 5. On-Resistance Variation with Temperature

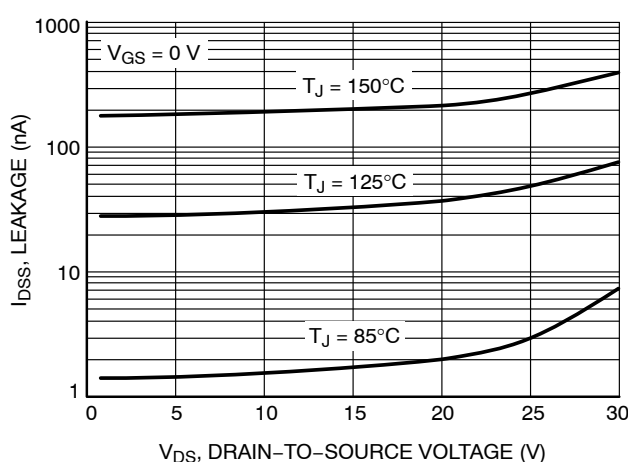


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL MOSFET CHARACTERISTICS

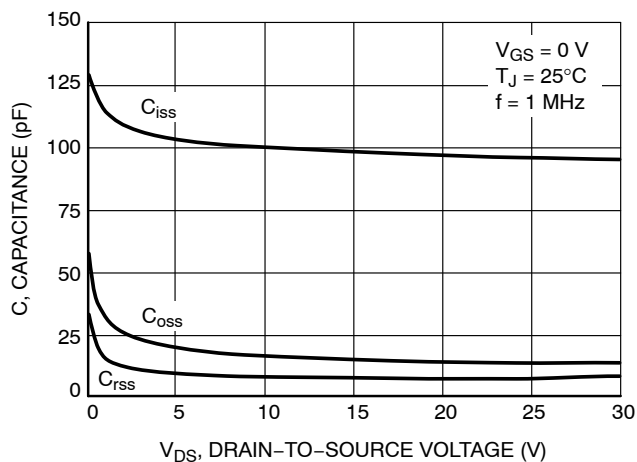


Figure 7. Capacitance Variation

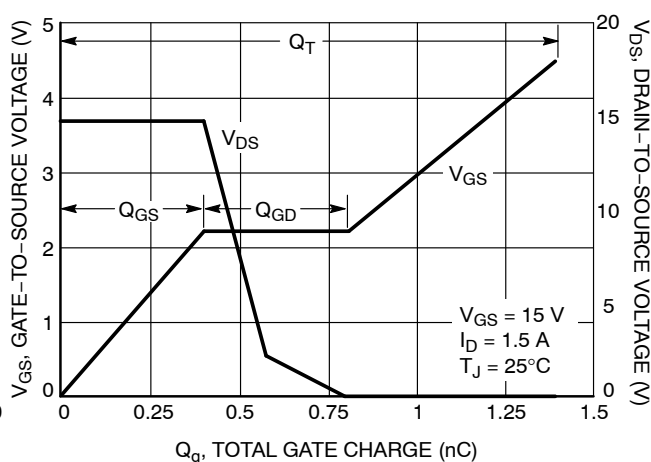


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

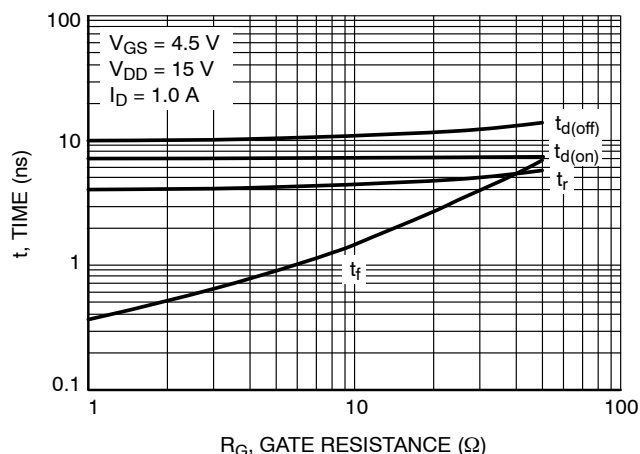


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

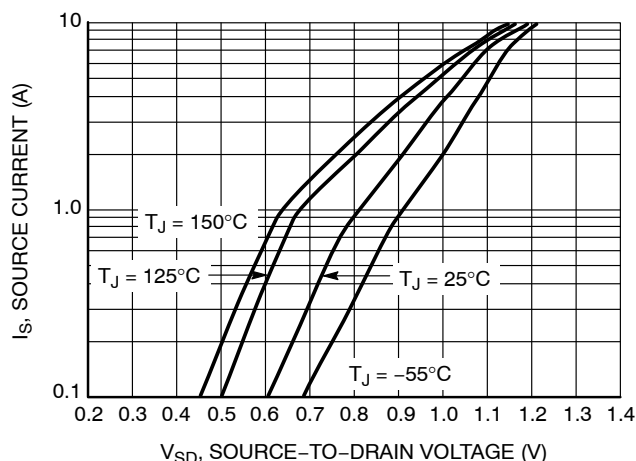


Figure 10. Diode Forward Voltage vs. Current

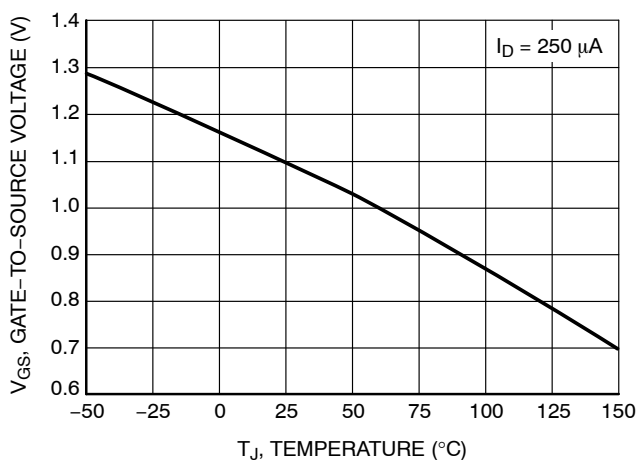


Figure 11. Threshold Voltage

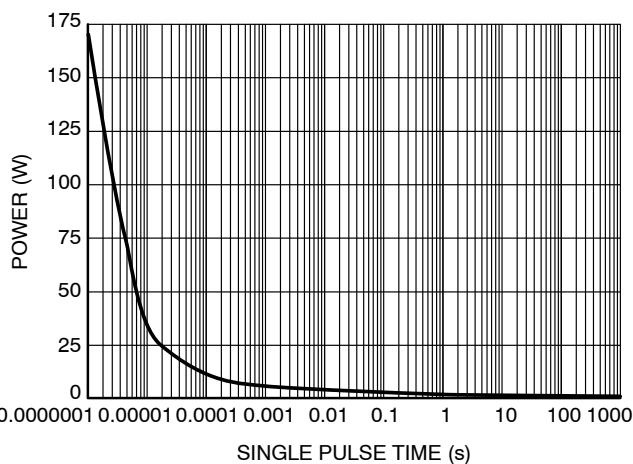


Figure 12. Single Pulse Maximum Power Dissipation

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TYPICAL MOSFET CHARACTERISTICS

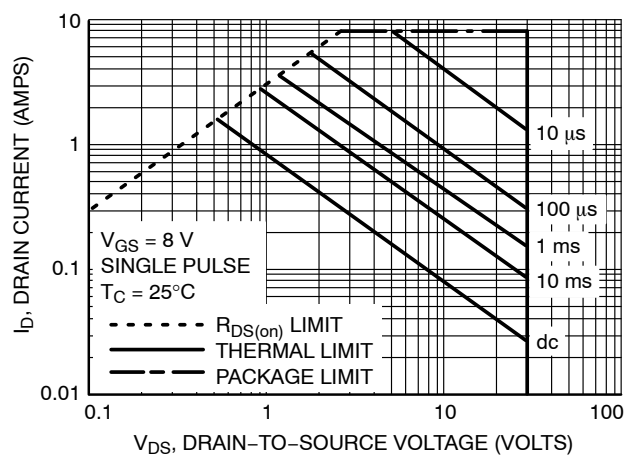


Figure 13. Maximum Rated Forward Biased Safe Operating Area

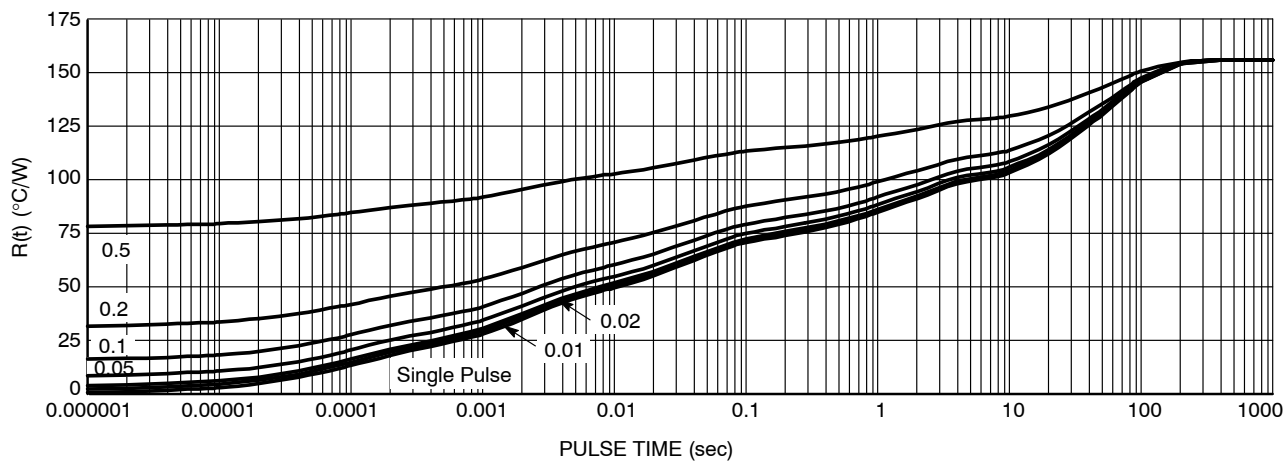


Figure 14. FET Thermal Response

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TYPICAL SCHOTTKY CHARACTERISTICS

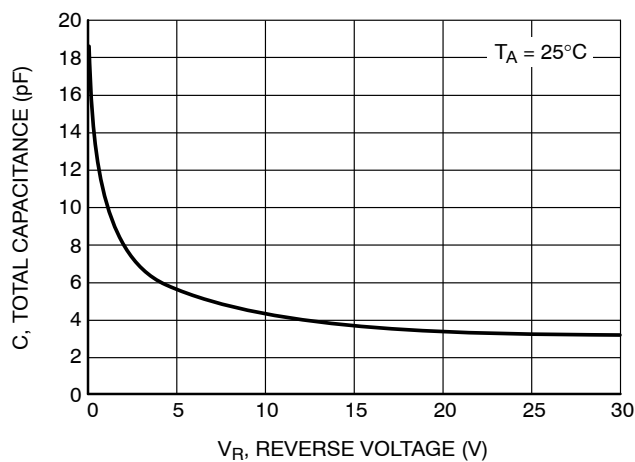


Figure 15. Total Capacitance

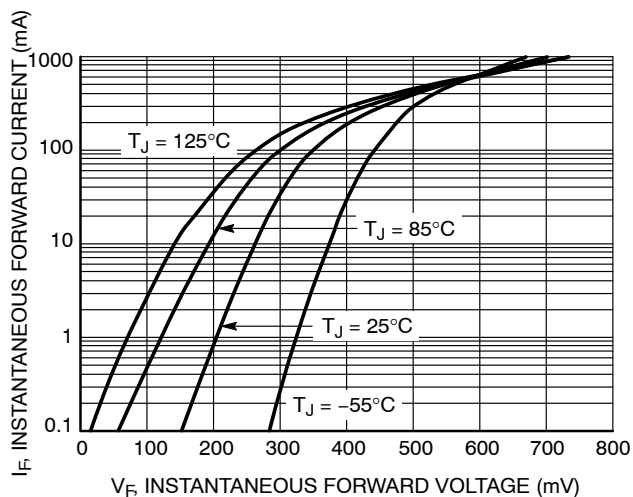


Figure 16. Typical Forward Voltage

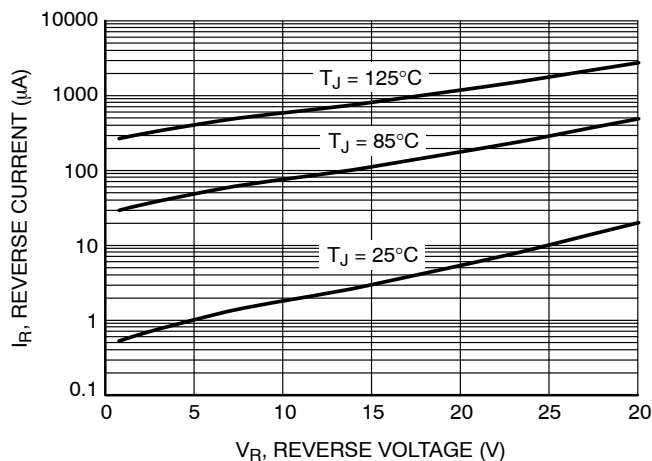


Figure 17. Typical Reverse Current

